# NSN 5961-01-075-5458

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# Inclosure Material:

Metal

**Overall Length:** 

1.252 inches

# **Overall Height:**

0.340 inches

**Overall Width:** 

0.700 inches

# Mounting Facility Quantity:

2

#### Internal Configuration:

Junction contact

#### Joint Electronic Device Engineering Council/jedec/case Outline Designation:

#### To-66

Electrode Internally-electrically Connected To Case:

Collector

#### Mounting Method:

Unthreaded hole

### Features Provided:

Hermetically sealed case

#### Semiconductor Material:

Silicon

#### Voltage Rating In Volts Per Characteristic:

80.0 breakdown voltage, collector-to-base, emitter open and 5.0 emitter to base voltage, static, collector open and 80.0 breakdown

voltage, collector-to-emitter, base open

#### **Current Rating Per Characteristic:**

3.00 amperes source cutoff current and 1.00 amperes source cutoff current

#### **Power Rating Per Characteristic:**

35.0 watts small-signal input power, common-collector

#### Transfer Ratio:

100.0 static forward current transfer ratio, common-emitter

# Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

# **Special Features:**

Junction pattern arrangement: npn

# **Terminal Type And Quantity:**

2 pin and 1 case

Shelf Life:

N/a

# Unit Of Measure:

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#### Demilitarization:

No

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